NSN 5961-01-350-1245

Diode Semiconductor Device - Page 1 of 1

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Inclosure Material:

Metal

Overall Length:

0.016 inches

Overall Height:

Between 0.005 inches and 0.008 inches

Overall Width:

0.016 inches

Function For Which Designed:

Switching

Mounting Method:

Press fit

Features Provided:

Mounting pad

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

100.0 breakdown voltage, dc

Current Rating Per Characteristic:

10.00 microamperes forward current, average peak

Power Rating Per Characteristic:

200.0 milliwatts small-signal input power, common-collector

Capacitance Rating In Picofarads:

0.1

Maximum Operating Tempurature Per Measurement Point:

85.0 degrees celsius ambient air

Special Features:

The diode shall be capable of fulfilling all requirements when attached to a gold plated aluminum ground plane using a conductive silver filled epoxy; junction pattern arrangement: pn

Precious Material And Location:

Terminal surfaces gold

Precious Material:

Gold

Terminal Type And Quantity:

1 bonding pad

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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